Optoelectronic Devices

Order code	Manufacturer code	Description
72-8968	n/a	PHOTOTRANSISTOR (RC)

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Kingbright®

NPN BLACK PLASTIC PHOTOTRANSISTOR

L-610MP4BT/BD

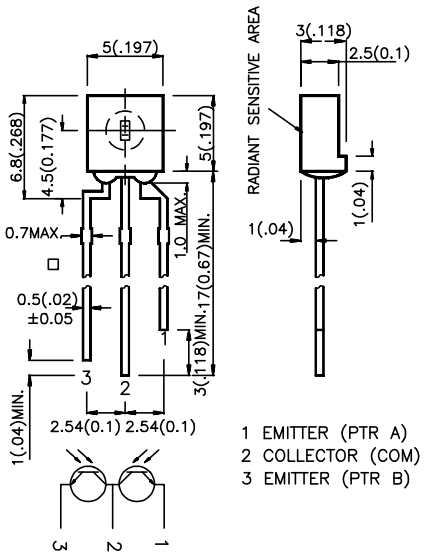
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE KM-4457 INFRARED EMITTING LED LAMP SERIES.
- BLACK PLASTIC PACKAGE.
- COUPLED WITH KM-4457 INFRARED EMITTING LED LAMP SERIES FOR MOUSE APPLICATION.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:
1. All dimensions are in millimeters (inches).
2. Tolerance is ±0.25(0.01") unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subjected to change without notice.

Absolute Maximum Ratings at T_A=25°C

Parameter	Maximum Rating
Collector-to-Emitter Breakdown Voltage	30V
Emitter-to-Collector Breakdown Voltage	5V
Power Dissipation at (or below) 25 °C Free Air Temperature	100mW
Operating Temperature Range	-55 °C ~ +85 °C
Storage Temperature Range	-55 °C ~ +85 °C
Lead Soldering Temperature (4mm for 5sec)	260 °C

Electrical and Radiant Characteristics T_A=25°C

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condiction
V_{BRCEO}	Collector-to-Emitter Breakdown Voltage	30	-	-	V	I_C=100uA E_e=0mW/cm²
V_{BRECO}	Emitter-to-Collector Breakdown Voltage	5	-	-	V	I_E=100uA E_e=0mW/cm²
$V_{CE(SAT)}$	Collector-to-Emitter Saturation Voltage	-	-	0.4	V	I_C=0.5mA E_e=5mW/cm²
I_{CEO}	Collector Dark Current	-	-	100	nA	V_{CE}=10V E_e=0mW/cm²
T_R	Rise Time (10% to 90%)	-	16	-	us	V_R=5V I_C=1mA R_L=1K ohms
T_F	Fall Time (90% to 10%)	-	18	-	us	
$I_{(ON)}$	On State Collector Current	0.12	-		mA	V_{CE}=5V E_e=1mW/cm² λ=940nm
R	Collector Current Ratio of 2 Phototransistor	0.8	1.0	1.25		Ic(on) (a) / Ic(on) (b)